METHOD OF RESIDUAL RESIST REMOVAL AFTER ETCHING OF ALUMINUM OR ALUMINUM ALLOY FILMS IN CHLORINE CONTAINING PLASMA

ABSTRACT

A method of removing remaining photoresist over an Al or Al alloy structure after etching the Al or Al alloy structure in chlorine based plasma, the Al or Al alloy structure being over a substrate, comprises the following steps. The photoresist, Al or Al alloy structure, and the substrate are treated in-situ with organic solvent vapors (such as acetone or carbon tetrachloride) in the absence of plasma excitation at a first predetermined temperature and pressure. The remaining photoresist is then removed with a plasma activated oxygen flow at a second predetermined temperature and pressure.

FIGURE 1